

General Description

The WSD100N06GDN56 is the SGT MOSFET with extreme high cell density, which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications.

The WSD100N06GDN56 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Lead Free and Green Devices Available (RoHS Compliant)
- 100% UIS + Rg Tested
- Reliable and Rugged
- Moisture Sensitivity Level MSL1 (per JED EC J-STD-020D)

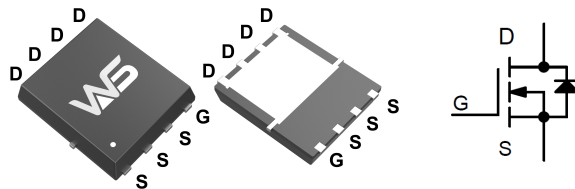
Product Summary

B_{VDSS}	$R_{DS(on)}$	I_D
60V	3.0m Ω	100A

Applications

- Secondary Side Synchronous Rectification
- DC-DC Converter
- Motor Control
- Load Switching

DFN5x6A-8_EP Pin Configuration



Absolute Maximum Ratings @ $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		60	V
V_{GS}	Gate-Source Voltage		± 20	V
$I_D^{1,6}$	Continuous Drain Current	$T_C=25^\circ\text{C}$	100	A
		$T_C=100^\circ\text{C}$	65	
I_{DM}^2	Pulsed Drain Current		$T_C=25^\circ\text{C}$	A
P_D	Maximum Power Dissipation		$T_C=25^\circ\text{C}$	W
			$T_C=100^\circ\text{C}$	
I_{AS}	Avalanche Current, Single pulse		45	A
E_{AS}^3	Single Pulse Avalanche Energy		101	mJ
T_J	Maximum Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55 to 150	$^\circ\text{C}$
$R_{\theta JA}^1$	Thermal Resistance Junction to ambient	Steady State	55	$^\circ\text{C}/\text{W}$
$R_{\theta JC}^1$	Thermal Resistance-Junction to Case	Steady State	1.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics @T_A=25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 48 V, V _{GS} = 0V			1	μA
		T _J =85°C			30	
I _{GSS}	Gate Leakage Current	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics						
V _{GS(TH)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _{DS} = 250μA	1.2	1.8	2.5	V
R _{DS(on)} ²	Drain-Source On-state Resistance	V _{GS} = 10V, I _D = 20A		3.0	3.6	mΩ
		V _{GS} = 4.5V, I _D = 15A		4.4	5.4	mΩ
Switching						
Q _g	Total Gate Charge	V _{DS} =30V V _{GS} =10V I _D =20A		58		nC
Q _{gs}	Gate-Source Charge			16		nC
Q _{gd}	Gate-Drain Charge			4.0		nC
t _{d(on)}	Turn-on Delay Time	V _{GEN} =10V V _{DD} =30V I _D =20A R _G =Ω		18		ns
t _r	Turn-on Rise Time			8		ns
t _{d(off)}	Turn-off Delay Time			50		ns
t _f	Turn-off Fall Time			11		ns
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.7		Ω
Dynamic						
C _{iss}	In Capacitance	V _{GS} =0V V _{DS} =30V f=1MHz		3458		pF
C _{oss}	Out Capacitance			1522		pF
C _{rss}	Reverse Transfer Capacitance			22		pF
Drain-Source Diode Characteristics and Maximum Ratings						
I _S ^{1,5}	Continuous Source Current	V _G =V _D =0V, Force Current			55	A
I _{SM}	Pulsed Source Current ³				240	A
V _{SD} ²	Diode Forward Voltage	I _{SD} = 1A, V _{GS} =0V		0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =20A, dI _{SD} /dt=100A/μs		27		ns
Q _{rr}	Reverse Recovery Charge				33	

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V_{DD}=50V, V_{GS}=10V, L=0.1mH, I_{AS}=40A
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.
- The maximum current rating is package limited.

Typical Operating Characteristics

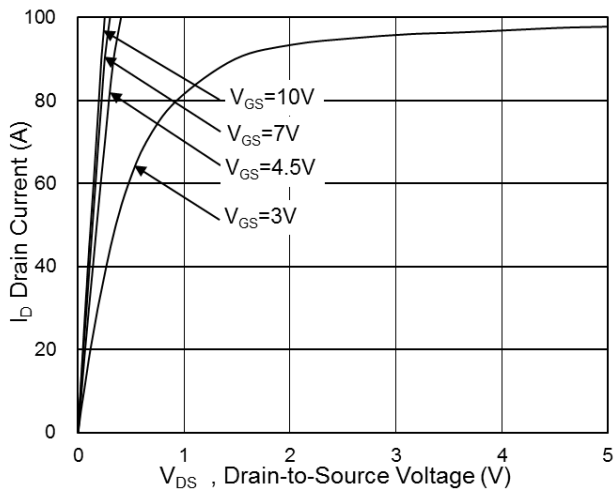


Fig.1 Typical Output Characteristics

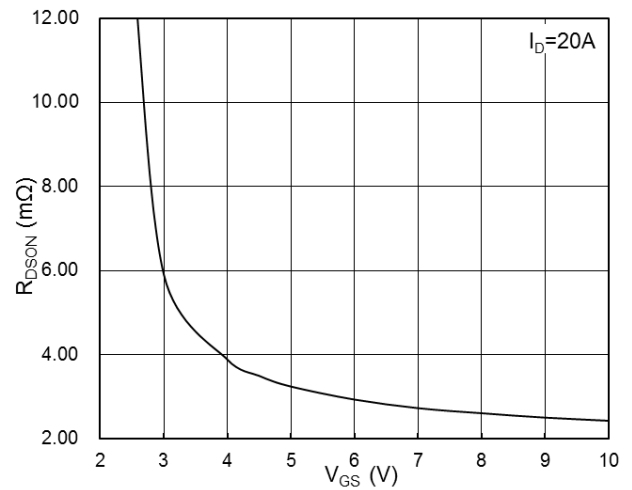


Fig.2 On-Resistance vs G-S Voltage

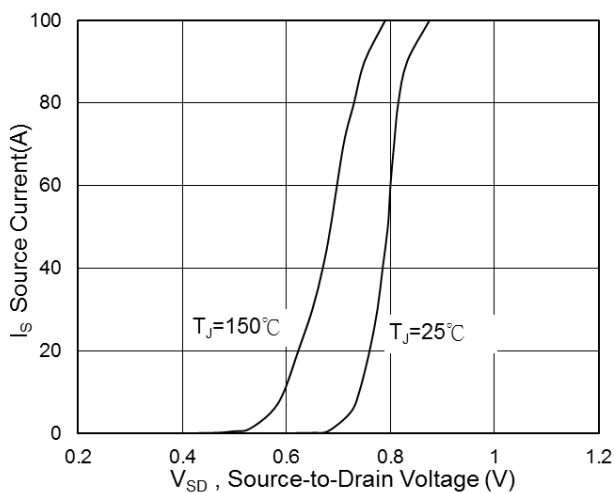


Fig.3 Diode Forward Voltage vs. Current

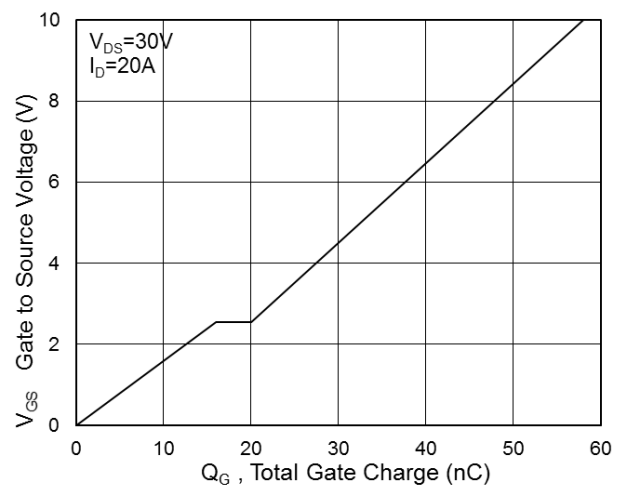


Fig.4 Gate-Charge Characteristics

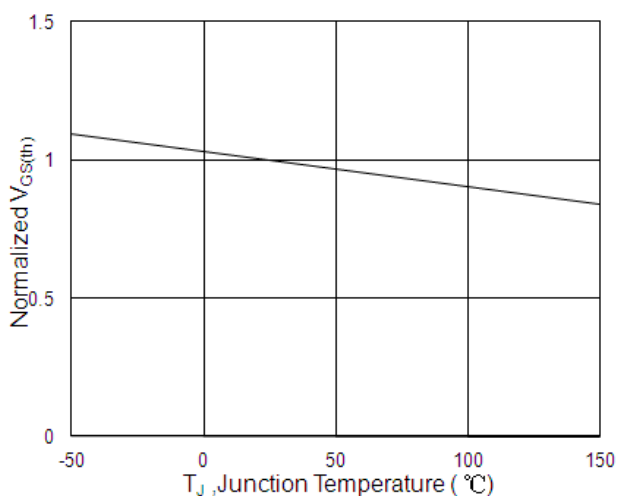


Fig.5 Normalized $V_{GS(th)}$ vs T_J

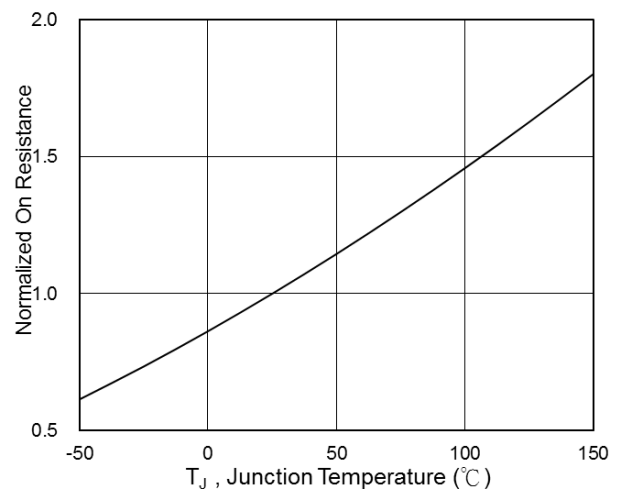


Fig.6 Normalized R_{DSON} vs T_J

Typical Operating Characteristics (Cont.)

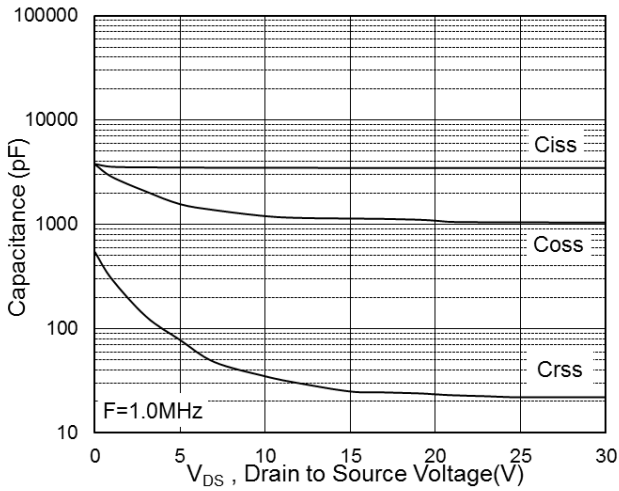


Fig.7 Capacitance

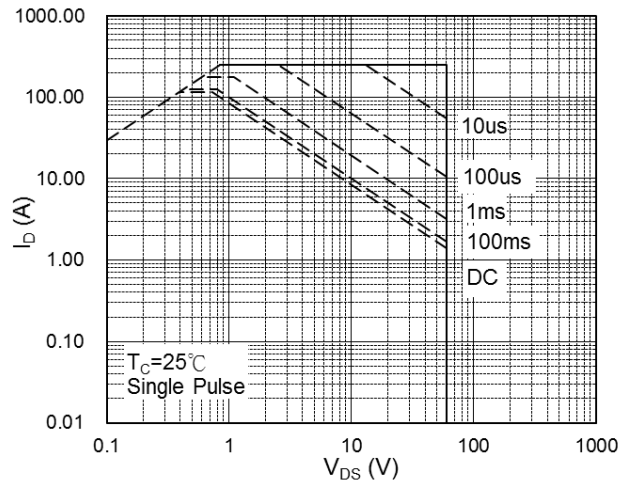


Fig.8 Safe Operating Area

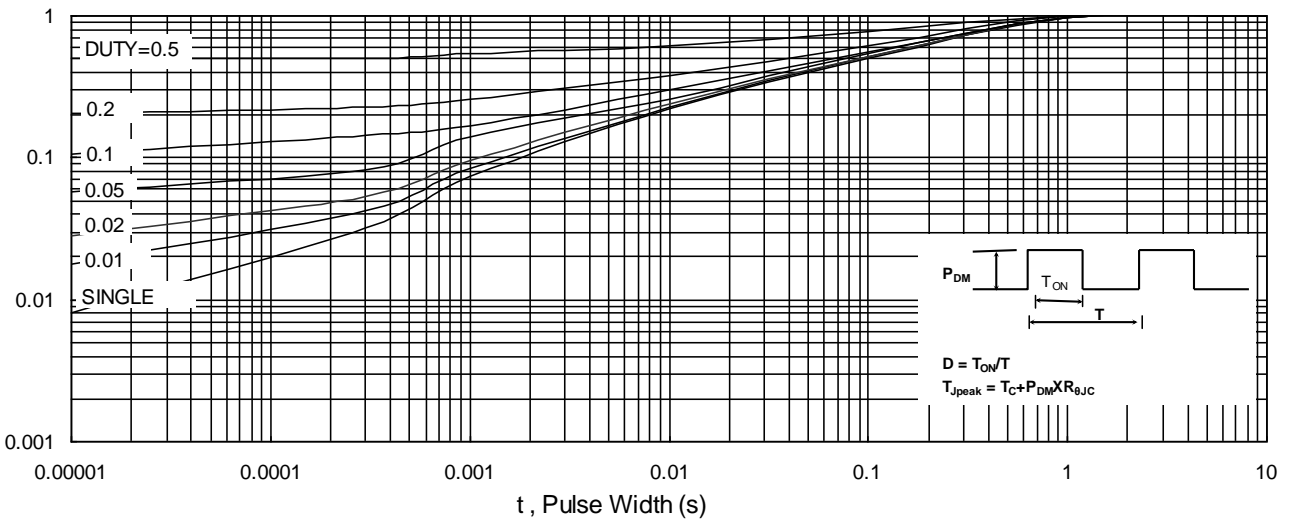


Fig.9 Normalized Maximum Transient Thermal Impedance

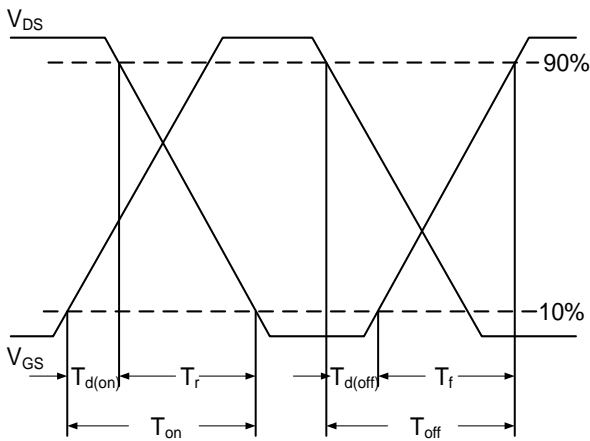


Fig.10 Switching Time Waveform

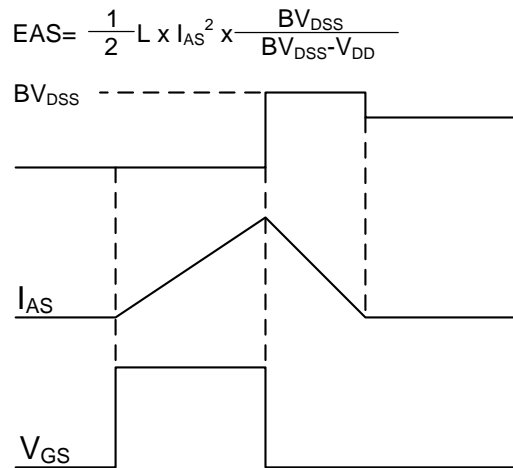


Fig.11 Unclamped Inductive Switching Waveform



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